

100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)} max	I _D max T _A = +25°C
400)/	150mΩ @ $V_{GS} = -10V$	-3.7A
-100V	190mΩ @ V _{GS} = -6V	-3.3A

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- · Relay and Solenoid Driving

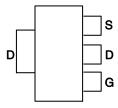
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

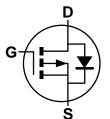
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

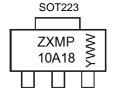
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP10A18GTA	ZXMP10A18	7	12	1,000

Note:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html

Marking Information



ZXMP10A18 =Product Type Marking Code YWW = Date Code Marking Y or Y= Last Digit of Year (ex: 5 = 2015) WW or WW = Week Code (01 - 53)





Maximum Ratings (@ $T_A = +25^{\circ}C$ unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-100	V
Gate-Source Voltage			V_{GSS}	±20	V
		(Note 6)		-3.7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	I _D	-3.0	Α
		(Note 5)		-2.6	
Pulsed Drain Current	$V_{GS} = 10V$	(Note 7)	I _{DM}	-16.5	Α
Continuous Source Current (Body diode) (Note 6)		(Note 6)	Is	-5.3	Α
Pulsed Source Current (Body diode) (Note 7)		I _{SM}	-16.5	Α	

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

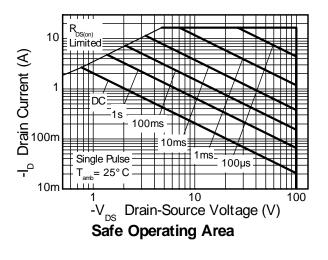
Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	0	2.0 16	W	
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/°C	
The second Description of the Architect	(Note 5)	-	62.5		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	32.2	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	$R_{ heta JL}$	7.65		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C	

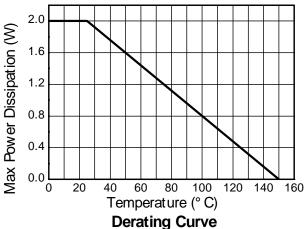
Notes:

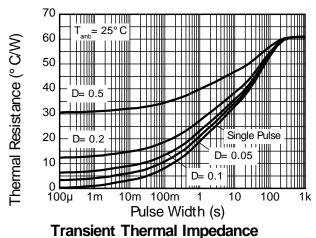
- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is measured at $t \le 10$ seconds.
- Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
 Thermal resistance from junction to solder-point (at the end of the drain lead).

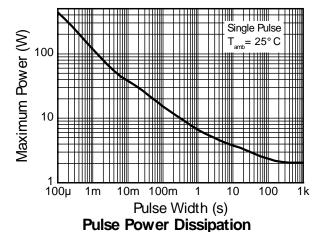


Thermal Characteristics













Electrical Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-100			V	$I_D = -250\mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_		-1	μΑ	$V_{DS} = -100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	-2.0	_	-4.0	V	$I_D = -250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	D			150	mΩ	$V_{GS} = -10V, I_D = -2.8A$	
Static Drain-Source On-Nesistance (Note 9)	R _{DS} (ON)	_		190	11122	$V_{GS} = -6V, I_D = -2.4A$	
Forward Transconductance (Notes 9 & 10)	g _{fs}	_	6.0		S	$V_{DS} = -15V$, $I_{D} = -2.8A$	
Diode Forward Voltage (Note 9)	V_{SD}	_	-0.85	-0.95	V	$I_S = -3.5A$, $V_{GS} = 0V$, $T_J = +25$ °C	
Reverse Recovery Time (Note 10)	t _{rr}		49	_	ns	$I_S = -2.8A$, di/dt = 100A/ μ s,	
Reverse Recovery Charge (Note 10)	Q_{rr}	_	107	_	nC	$T_J = +25^{\circ}C$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1055		pF	,, 50,/,,/, 0,/	
Output Capacitance	Coss	_	90	_	pF	$V_{DD} = -50V, V_{GS} = 0V$ -f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	76	_	pF	1 = 11/1112	
Total Gate Charge (Note 11)	Qg	_	26.9	_	nC	$V_{GS} = -10V, V_{DS} = -50V$ $I_{D} = -2.8A$	
Gate-Source Charge (Note 11)	Qgs	_	3.9	_	nC		
Gate-Drain Charge (Note 11)	Q_{qd}	_	10.2	_	nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	4.6	_	ns		
Turn-On Rise Time (Note 11)	t _r	_	6.8	_	ns	$V_{DD} = -50V, V_{GS} = -10V$ $I_{D} = -1A, R_{G} \cong 6.0\Omega$	
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	33.9	_	ns		
Turn-Off Fall Time (Note 11)	t _f	_	17.9	_	ns		

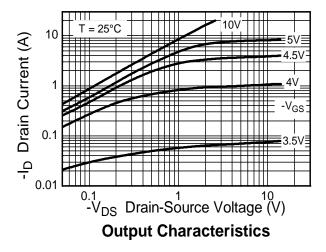
Notes:

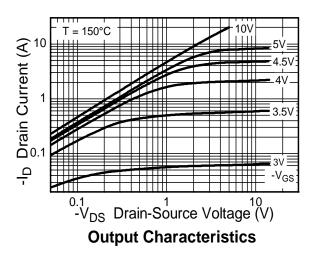
^{9.} Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%$

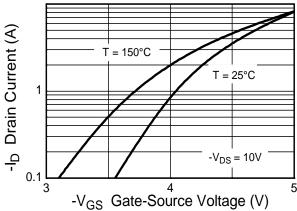
^{10.} For design aid only, not subject to production testing.
11. Switching characteristics are independent of operating junction temperatures.

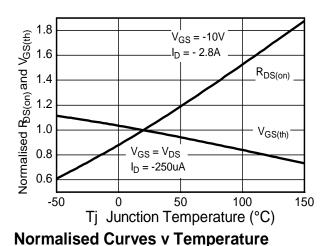


Typical Characteristics

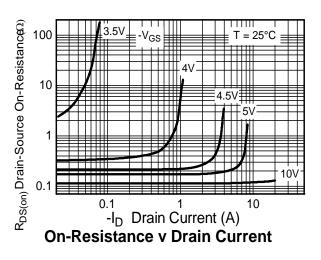


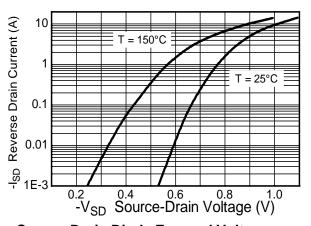






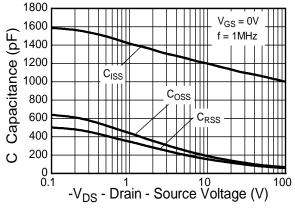
Typical Transfer Characteristics



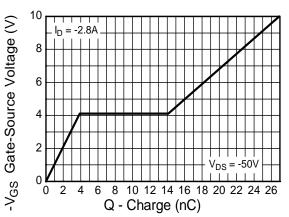


Source-Drain Diode Forward Voltage

Typical Characteristics (cont.)

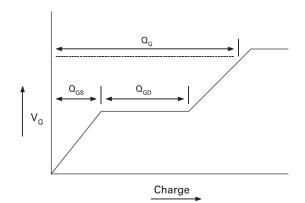


Capacitance v Drain-Source Voltage

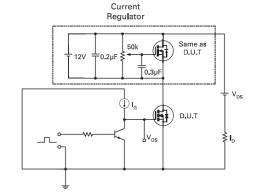


Gate-Source Voltage v Gate Charge

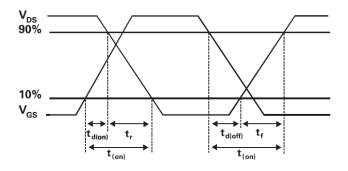
Test Circuits



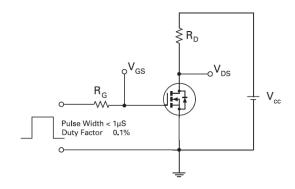
Basic Gate Charge Waveform



Gate Charge Test Circuit



Switching Time Waveforms



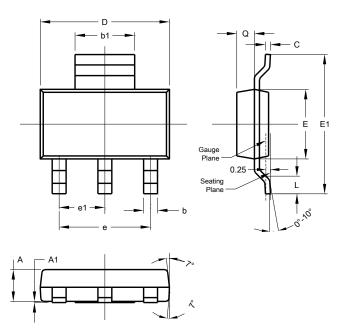
Switching Time Test Circuit





Package Outline Dimensions

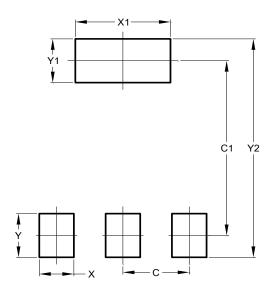
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	•	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00





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